

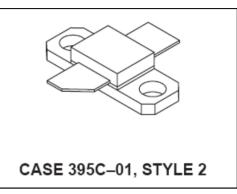
The RF Line NPN Silicon Power Transistor 6.0W , 1.6GHz, 28V

Rev. V1

Designed for 28 V microwave large–signal, common base, Class C, CW amplifier applications in the range 1600 – 1640 MHz.

- Specified 28 V, 1.6 GHz Class C characteristics Output power = 6 W Minimum gain = 7.4 dB, @ 6 W Minimum efficiency = 40% @ 6 W
- Characterized with series equivalent large–signal parameters from 1500 MHz to 1700 MHz
- Silicon nitride passivated
- Gold metalized, emitter ballasted for long life and resistance to metal migration

Product Image



MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CES}	60	Vdc
Emitter–Base Voltage	V _{EBO}	4.0	Vdc
Collector-Current	I _C	1.0	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	26 0.15	Watts W/ºC
Storage Temperature Range	T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case (1) (2)	R _{eJC}	6.8	°C/W
	,		

(1) Thermal measurement performed using CW RF operating condition.

(2) Thermal resistance is determined under specified RF operating conditions by infrared measurement techniques.

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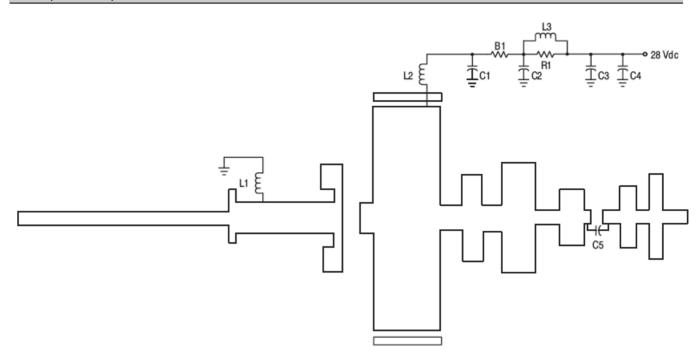
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	1		1	1	
Collector–Emitter Breakdown Voltage (I _C = 40 mAdc, V _{BE} = 0)	V _{(BR)CES}	55	_	_	Vdc
Collector–Base Breakdown Voltage (I _C = 40 mAdc, I _E = 0)	V _(BR) CBO	55	_	_	Vdc
Emitter–Base Breakdown Voltage (I _E = 2.5 mAdc, I _C = 0)	V _{(BR)EBO}	4.0	_	_	Vdc
Collector Cutoff Current (VCE = 28 Vdc, V _{BE} = 0)	I _{CES}	_	_	2.5	mAdc
ON CHARACTERISTICS	•				
DC Current Gain (I _{CE} = 0.2 Adc, V _{CE} = 5.0 Vdc)	h _{FE}	20	_	80	-
DYNAMIC CHARACTERISTICS		•			
Output Capacitance (V _{CB} = 28 Vdc, f = 1.0 MHz)	C _{ob}	11	_	_	pf
FUNCTIONAL TESTS		•	•	1	
Common–Base Amplifier Power Gain (V _{CC} = 28 Vdc, P _{out} = 6 Watts, f = 1600/1640 MHz)	G _{pe}	7.4	_	_	dB
Collector Efficiency (V _{CC} = 28 Vdc, P _{out} = 6 Watts, f = 1600/1640 MHz)	η	40	45	_	%
Return Loss (V _{CC} = 28 Vdc, P _{out} = 6 Watts, f = 1600/1640 MHz)	I _{RL}	_	8.0	_	dB
Output Mismatch Stress (V _{CC} = 28 Vdc, P _{out} = 6 Watts, f = 1600 MHz, Load VSWR = 3:1 all phase angles at frequency of test)	Ψ	No Degradation in Output Power			

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Board Material – Teflon[®] Glass Laminate Dielectric Thickness – 0.30", $\epsilon_{\rm r}$ = 2.55", 2.0 oz. Copper

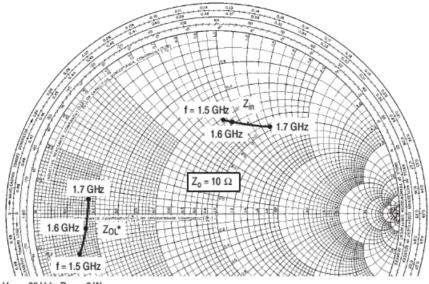


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V_{CC} = 28 Vdc, P_{out} = 6 W

f MHz	Z _{in} Ohms	Z _{OL} * Ohms
1500	6.28 + j 8.53	1.22 – j 1.37
1600	7.04 + j 9.00	1.58 – j 0.53
1700	9.55 + j 12.86	1.71 + j 0.39

 Z_{OL}^{\star} = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Figure 2. Series Equivalent Input/Output Impedance

MRF16006



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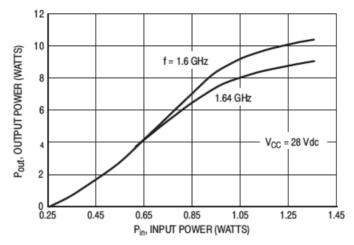


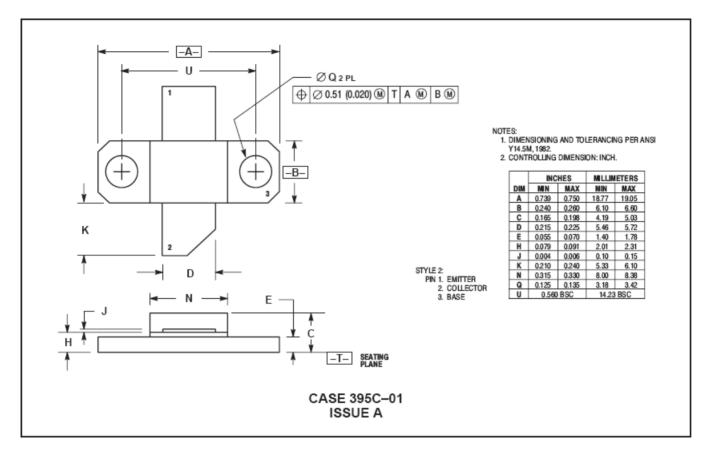
Figure 3. Output Power versus Input Power



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PACKAGE DIMENSIONS



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